



M T2 & T6 T

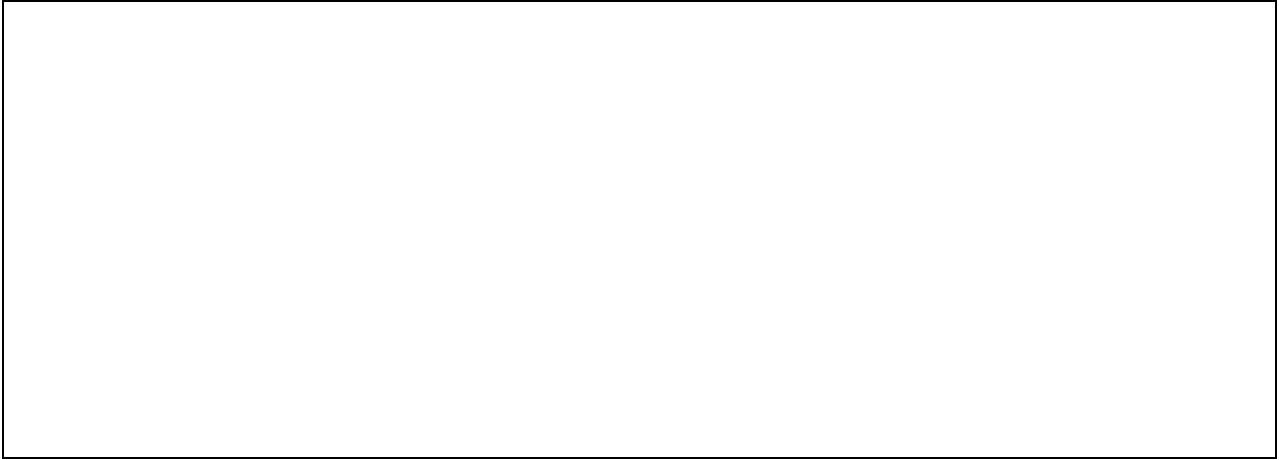


(@ $T_C = 25^\circ\text{C}$ unless otherwise specified)

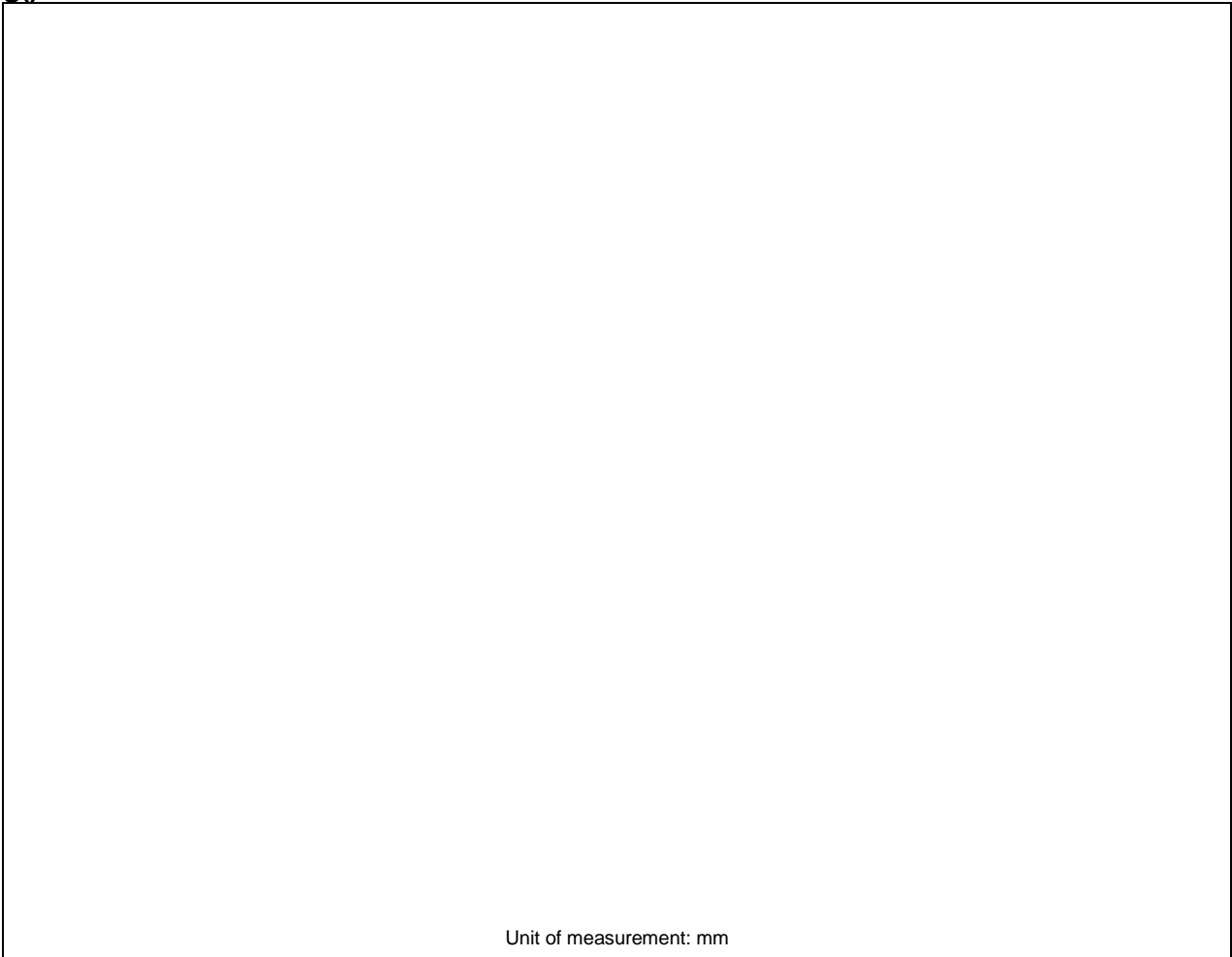
Parameter	Conditions	Symbol	Value			Unit
			Min	Typ	Max	
Peak forward voltage	$I_T=360\text{A}, t_P=380$	V_T			1.80	V
Repetitive peak off-state current	$V_D = V_{DRM}, T_{vj} = 25$	I_{DRM}			100	A
	$V_D = V_{DRM}, T_{vj} = 125$				40	mA
Reverse leakage current	$V_R = V_{RRM}, T_{vj} = 25$	I_{RRM}			100	A
	$V_R = V_{RRM}, T_{vj} = 125$				40	mA
Threshold voltage	For power loss calculation only $T_{vj} = 125$	V_{TO}			0.9	V
Dynamic resistance	$T_{vj} = 125$	r_T			2	
Triggering gate current	$V_D=12\text{V } R_L$	ITO				



④




⑤



Unit of measurement: mm



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